FM20N50

N-Channel Trench Power MOSFET

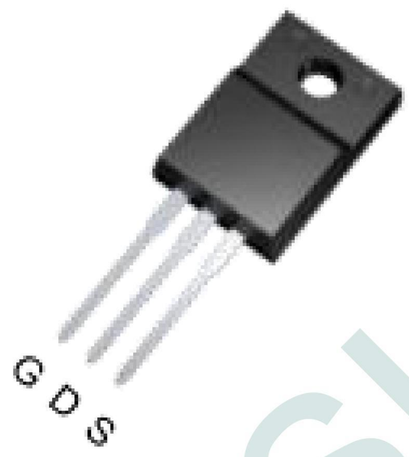
Features

- 500V/20A ,RDS(on) =0.23Ω@Tey ,VGS=10V
- Fast Switching
- Improved dv/dr capability
- Lead free product is acquired
- Excellent Rds (ON) and Low Gate Charge

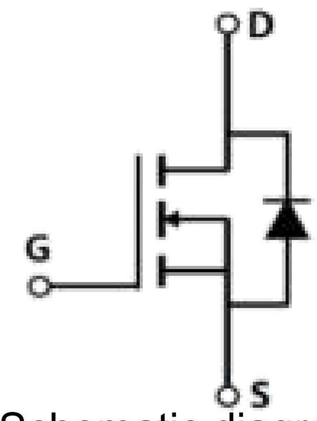
Application

- PWM applications
- Load Switch
- Power management

Package



TO-220F



Schematic diagram

Absolute Max Ratings at Ta=25℃ (Note1)

Parameter		Symbol	Value	Units
Drain to Source Voltage		Vds	500	V
Gate to Source Voltage		Vgs	±30	V
Drain Current (DC)	Ta=25℃	Id	20	A
	Ta=100℃		13	A
Drain Current (Pulse), PW≤300μs		Idp	80	A
Total Dissipation		Pd	45	W
Avalanche Energy, Single Pulsed		Eas	1400	mJ
Junction Temperature		Tj	-55 to +150	℃
Storage Temperature		Tstg	-55 to +150	℃

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